

AMENDMENT TO THE SUBSTITUTE SPECIFICATION:

Please amend the paragraph beginning on page 6, line 19, and ending on page 7, line 3, as follows:

FIG. 1 shows an apparatus for forming patterns according to this invention. In FIG. 1, numeral 103 indicates a sample stand for placing a substrate (sample) 107 to be processed, numeral 102 indicates a stage for placing a mask 106 for exposure, and numeral 101 indicates a light source and numeral 105 indicates a light for exposure. Light for exposure is, of course, adjusted to cover over the whole exposure region, and, more suitably, may be adjusted to enter perpendicularly to a film for improving energy efficiency. In FIG. 1, numeral 104 indicates distance-controlling means for controlling a distance between the photoresist and the photomask 106.

Please amend the paragraph beginning on page 16, line 18, and ending on page 17, line 4, as follows.

On a glass plate 640 650 as a photomask photo substrate, an Al thin film 651 is formed to a thickness of 36 nm as a shielding film by sputtering. As shown in FIG. 6A, while pushing the needle tip of a cantilever 652 for AFM with an elastic constant of 45 N/m against the thin film at a pressure of about  $1 \times 10^{-5}$  N, the Al thin film 651 is scanned with the cantilever to form a minute aperture 653 with an opening width of about 100 nm (FIG. 6B). The cantilever 652 AFM

is moved several times while pushing its needle tip against a Ti film to blunt the needle tip. Then, while pushing the blunted needle tip against the Al thin film 651 at a pressure of about  $5 \times 10^{-5}$  N, the Al thin film 651 is scanned with the cantilever as described above to form an aperture 654 with an opening width of 1  $\mu$ m.

Please amend the paragraph beginning on page 18, line 1, and ending on page 18, line 4, as follows:

Since a light quantity from a minute aperture 213 with a pattern width of 100 nm is considerably lower than a light quantity from an aperture 214, exposure adjusted for the minute aperture 213 may make a photoresist pattern 217 by exposure from the aperture ~~214~~ 222 larger than the aperture 214.